

A2, cont  
portion by development.

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A3  
29. (Amended) The resist pattern according to Claim 24, wherein a width of the resist pattern is 1  $\mu\text{m}$  or more.

30. (Amended) The resist pattern according to Claim 24, wherein a height of the resist pattern is 1 to 150  $\mu\text{m}$ .

31. (Amended) The resist pattern laminated substrate which comprises the resist pattern according to Claim 24, wherein it is formed on a substrate for preparing a circuit.

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A4  
40. (Amended) The wiring pattern according to Claim 34, wherein a height of the wiring pattern is 0.01 to 200  $\mu\text{m}$ .

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